

LC²MOS Precision Quad SPST Switches

ADG431/ADG432/ADG433

FEATURES

44 V Supply Maximum Ratings
±15 V Analog Signal Range
Low On Resistance (<24 Ω)
Ultralow Power Dissipation (3.9 μW)
Low Leakage (<0.25 nA)
Fast Switching Times
t_{ON} <165 ns
t_{OFF} <130 ns
Break-Before-Make Switching Action
TTL/CMOS Compatible
Plug-in Replacement for DG411/DG412/DG413

APPLICATIONS

Audio and Video Switching Automatic Test Equipment Precision Data Acquisition Battery Powered Systems Sample Hold Systems Communication Systems

GENERAL DESCRIPTION

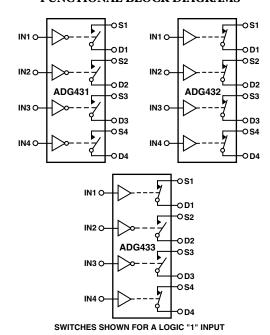
The ADG431, ADG432 and ADG433 are monolithic CMOS devices comprising four independently selectable switches. They are designed on an enhanced LC²MOS process which provides low power dissipation yet gives high switching speed and low on resistance.

The on resistance profile is very flat over the full analog input range ensuring excellent linearity and low distortion when switching audio signals. Fast switching speed coupled with high signal bandwidth also make the parts suitable for video signal switching. CMOS construction ensures ultralow power dissipation making the parts ideally suited for portable and battery powered instruments.

The ADG431, ADG432 and ADG433 contain four independent SPST switches. The ADG431 and ADG432 differ only in that the digital control logic is inverted. The ADG431 switches are turned on with a logic low on the appropriate control input, while a logic high is required for the ADG432. The ADG433 has two switches with digital control logic similar to that of the ADG431 while the logic is inverted on the other two switches.

Each switch conducts equally well in both directions when ON and has an input signal range which extends to the supplies. In the OFF condition, signal levels up to the supplies are blocked. All switches exhibit break before make switching action for use in multiplexer applications. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

FUNCTIONAL BLOCK DIAGRAMS



PRODUCT HIGHLIGHTS

1. Extended Signal Range
The ADG431 ADG432 an

The ADG431, ADG432 and ADG433 are fabricated on an enhanced LC²MOS process giving an increased signal range which extends fully to the supply rails.

- 2. Ultralow Power Dissipation
- 3. Low Ron
- 4. Break-Before-Make Switching
 This prevents channel shorting when the switches are configured as a multiplexer.
- 5. Single Supply Operation
 For applications where the analog signal is unipolar, the ADG431, ADG432, and ADG433 can be operated from a single rail power supply. The parts are fully specified with a single 12 V power supply and will remain functional with single supplies as low as 5 V.

REV. C

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ADG431/ADG432/ADG433—SPECIFICATIONS¹

Dual Supply ($V_{DD}=+15~V~\pm~10\%,~V_{SS}=-15~V~\pm~10\%,~V_L=+5~V~\pm~10\%,~GND=0~V,~unless~otherwise~noted.$)

	BV	ersion		
Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		$ m V_{DD}$ to $ m V_{SS}$	V	
R_{ON}	17	DD 33	Ω typ	$V_D = \pm 8.5 \text{ V}, I_S = -10 \text{ mA};$
	24	26	Ω max	$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$
R_{ON} vs. V_D (V_S)	15		% typ	
R _{ON} Drift	0.5		%/°C typ	
R _{ON} Match	5		% typ	$V_D = 0 \text{ V}, I_S = -10 \text{ mA}$
LEAKAGE CURRENTS				$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
Source OFF Leakage I _S (OFF)	±0.05		nA typ	$V_D = \pm 15.5 \text{ V}, V_S = \pm 15.5 \text{ V};$
	±0.25	±2	nA max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.05		nA typ	$V_D = \pm 15.5 \text{ V}, V_S = \mp 15.5 \text{ V};$
	±0.25	±2	nA max	Test Circuit 2
Channel ON Leakage I _D , I _S (ON)	±0.1	±2	nA typ	$V_D = V_S = \pm 15.5 \text{ V};$
	±0.35	±3	nA max	Test Circuit 3
DIGITAL INPUTS		2.4		
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current I_{INL} or I_{INH}	0.005		u A tro	$V_{IN} = V_{INI}$ or V_{INH}
I _{INL} of I _{INH}	0.003	±0.02	μΑ typ μΑ max	VIN - VINL OI VINH
C _{IN} Digital Input Capacitance	9	±0.02	pF typ	
			Pr tjp	V - 115 V V - 15 V
DYNAMIC CHARACTERISTICS ¹	90			$V_{DD} = +15 \text{ V}, V_{SS} = -15 \text{ V}$ $R_L = 300 \Omega, C_L = 35 \text{ pF};$
t_{ON}	90	165	ns typ ns max	$V_S = \pm 10 \text{ V}$; Test Circuit 4
$t_{ m OFF}$	60	105	ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$;
OFF		130	ns max	$V_S = \pm 10 \text{ V}$; Test Circuit 4
Break-Before-Make Time Delay, t _D	25		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
(ADG433 Only)				$V_{S1} = V_{S2} = +10 \text{ V};$
				Test Circuit 5
Charge Injection	5		pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 10 \text{ nF};$
				Test Circuit 6
OFF Isolation	68		dB typ	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz;$
Channel to Channel Cassatalla	0.5		dD 4	Test Circuit 7
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; Test Circuit 8
C_S (OFF)	9		pF typ	f = 1 MHz
$C_{\rm D}$ (OFF)	9		pF typ	f = 1 MHz
$C_D, C_S (ON)$	35		pF typ	f = 1 MHz
POWER REQUIREMENTS				$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
TOWER REQUIREMENTS				Digital Inputs = $0 \text{ V or } 5 \text{ V}$
I_{DD}	0.0001		μA typ	8 0 . 01 3 .
	0.1	0.2	μA max	
${ m I}_{ m SS}$	0.0001		μA typ	
	0.1	0.2	μA max	
${ m I_L}$	0.0001		μA typ	
	0.1	0.2	μA max	
Power Dissipation		7.7	μW max	

NOTES

Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

Single Supply (V_DD = 12 V \pm 10%, V_SS = 0 V, V_L = 5 V \pm 10%, GND = 0 V, unless otherwise noted)

	BV	ersion ersion		
Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH	1200			2 000 00210201010100100
Analog Signal Range		0 V to V _{DD}	V	
	28	O V to VDD	ν Ω typ	$0 < V_D < 8.5 \text{ V}, I_S = -10 \text{ mA};$
R_{ON}	42	45	Ω max	$V_{DD} = 10.8 \text{ V}$
R_{ON} vs. V_D (V_S)	20	4)	% typ	V _{DD} = 10.8 V
R _{ON} vs. v _D (v _S) R _{ON} Drift	0.5		% typ %/°C typ	
R _{ON} Match	5		% typ	$V_D = 0 \text{ V}, I_S = -10 \text{ mA}$
-	'		70 typ	-
LEAKAGE CURRENTS	1004			$V_{\rm DD} = 13.2 \text{ V}$
Source OFF Leakage I _S (OFF)	±0.04		nA typ	$V_D = 12.2/1 \text{ V}, V_S = 1/12.2 \text{ V};$
	±0.25	±2	nA max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.04		nA typ	$V_D = 12.2/1 \text{ V}, V_S = 1/12.2 \text{ V};$
	±0.25	±2	nA max	Test Circuit 2
Channel ON Leakage I _D , Is (ON)	±0.01		nA typ	$V_D = V_S = 12.2 \text{ V/1 V};$
	±0.3	±3	nA max	Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current				
I _{INL} or I _{INH}	0.005		μA typ	$V_{IN} = V_{INI}$ or V_{INH}
IND INI		± 0.01	μA max	
C _{IN} Digital Input Capacitance	9		pF typ	
DYNAMIC CHARACTERISTICS ¹				$V_{\rm DD} = 12 \text{ V}, V_{\rm SS} = 0 \text{ V}$
ton	165		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
ON		240	ns max	$V_S = 8 \text{ V}$; Test Circuit 4
t _{OFF}	60	-10	ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF;$
Off		115	ns max	$V_S = 8 \text{ V}$; Test Circuit 4
Break-Before-Make Time Delay, t _D	25	113	ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF;$
(ADG433 Only)			no typ	$V_{S1} = V_{S2} = 10 \text{ V}$; Test Circuit 5
Charge Injection	25		pC typ	$V_{S} = 0 \text{ V}, R_{S} = 0 \Omega, C_{L} = 10 \text{ nF};$
Charge Injection	23		potyp	Test Circuit 6
OFF Isolation	68		dB typ	$R_{L} = 50 \Omega, C_{L} = 5 pF, f = 1 MHz$
			dD typ	Test Circuit 7
Channel-to-Channel Crosstalk	85		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$
Chainer to Chainer Growtan			uz typ	Test Circuit 8
C _s (OFF)	9		pF typ	f = 1 MHz
C_{D} (OFF)	9		pF typ	f = 1 MHz
C_D , C_S (ON)	35		pF typ	f = 1 MHz
	+ 33		Pr typ	
POWER REQUIREMENTS				$V_{DD} = 13.2 \text{ V}$
т	0.0001			Digital Inputs = 0 V or 5 V
$I_{ m DD}$	0.0001	0.1	μA typ	
.	0.03	0.1	μA max	
$I_{\rm L}$	0.0001		μA typ	
D D' ' '	0.03	0.1	μA max	$V_{L} = 5.25 \text{ V}$
Power Dissipation		1.9	μW max	

NOTES

Specifications subject to change without notice.

Truth Table (ADG431/ADG432)

ADG431 In	ADG432 In	Switch Condition
0	1	ON
1	0	OFF

Truth Table (ADG433)

Logic	Switch 1, 4	Switch 2, 3
0	OFF	ON
1	ON	OFF

REV. C -3-

¹Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

$(T_A = 25^{\circ}C \text{ unless otherwise noted.})$
V_{DD} to V_{SS}
V_{DD} to GND0.3 V to +25 V
V_{SS} to GND +0.3 V to –25 V
V_L to GND
Analog, Digital Inputs ² V_{SS} – 2 V to V_{DD} + 2 V or
30 mA, Whichever Occurs First
Continuous Current, S or D
Peak Current, S or D
(Pulsed at 1 ms, 10% Duty Cycle max)
Operating Temperature Range
Industrial (B Version)40°C to +85°C
Storage Temperature Range65°C to +150°C
Junction Temperature

Plastic Package, Power Dissipation 470 mW
θ_{JA} , Thermal Impedance
Lead Temperature, Soldering (10 sec) 260°C
SOIC Package, Power Dissipation 600 mW
θ_{IA} , Thermal Impedance
Lead Temperature, Soldering
Vapor Phase (60 sec)
Infrared (15 sec)

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

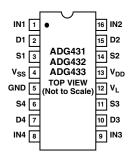
²Overvoltages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

CAUTION_

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG431/ADG432/ADG433 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



PIN CONFIGURATION (DIP/SOIC)



ORDERING GUIDE

Model	Temperature Range	Package Option ¹
ADG431BN	-40°C to +85°C	N-16
ADG431BR	−40°C to +85°C	R-16A
ADG431ABR	−40°C to +85°C	R-16A ²
ADG432BN	−40°C to +85°C	N-16
ADG432BR	−40°C to +85°C	R-16A
ADG432ABR	-40°C to +85°C	R-16A ²
ADG433BN	−40°C to +85°C	N-16
ADG433BR	−40°C to +85°C	R-16A
ADG433ABR	–40°C to +85°C	R-16A ²

NOTES

¹N = Plastic DIP; R = 0.15" Small Outline IC (SOIC).

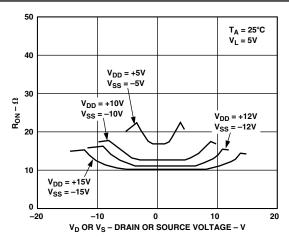
TERMINOLOGY

$V_{ m DD}$	Most positive power supply potential.	C_S (OFF)	"OFF" switch source capacitance.
V_{SS}	Most negative power supply potential in dual	C_D (OFF)	"OFF" switch drain capacitance.
	supplies. In single supply applications, it may be	C_D , C_S (ON)	"ON" switch capacitance.
	connected to GND.	C_{IN}	Input Capacitance to ground of a digital input.
$ m V_L$	Logic power supply (5 V).	t_{ON}	Delay between applying the digital control input
GND	Ground (0 V) reference.		and the output switching on.
S	Source terminal. May be an input or output.	t_{OFF}	Delay between applying the digital control input
D	Drain terminal. May be an input or output.		and the output switching off.
IN	Logic control input.	t_{D}	"OFF" time or "ON" time measured between the
R_{ON}	Ohmic resistance between D and S.		90% points of both switches, when switching
R_{ON} vs. V_D (V_S)	The variation in R _{ON} due to a change in the ana-		from one address state to another.
	log input voltage with a constant load current.	Crosstalk	A measure of unwanted signal which is coupled
R _{ON} Drift	Change in R _{ON} vs. temperature.		through from one channel to another as a result
R _{ON} Match	Difference between the R _{ON} of any two switches.		of parasitic capacitance.
I _S (OFF)	Source leakage current with the switch "OFF."	Off Isolation	A measure of unwanted signal coupling through an
I_D (OFF)	Drain leakage current with the switch "OFF."		"OFF" switch.
$I_D, I_S (ON)$	Channel leakage current with the switch "ON."	Charge	A measure of the glitch impulse transferred from the
$V_{\rm D} (V_{\rm S})$	Analog voltage on terminals D, S.	Injection	digital input to the analog output during switching.

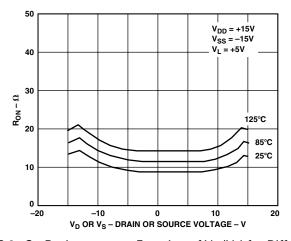
–4– REV. C

²Trench isolated, latch-up proof parts. See Trench Isolation section.

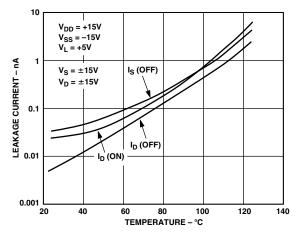
Typical Performance Characteristics—ADG431/ADG432/ADG433



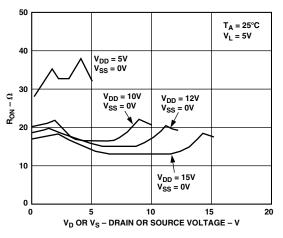
TPC 1. On Resistance as a Function of V_D (V_S) Dual Supplies



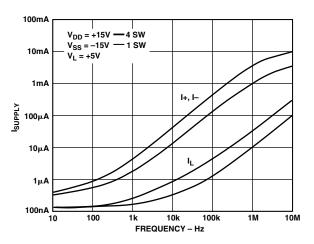
TPC 2. On Resistance as a Function of $V_D \, (V_S)$ for Different Temperatures



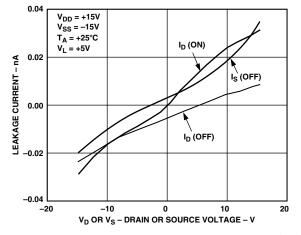
TPC 3. Leakage Currents as a Function of Temperature



TPC 4. On Resistance as a Function of V_D (V_S) Single Supply

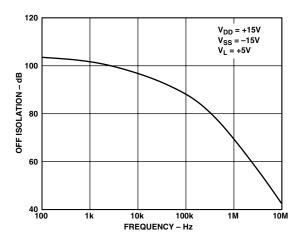


TPC 5. Supply Current vs. Input Switching Frequency

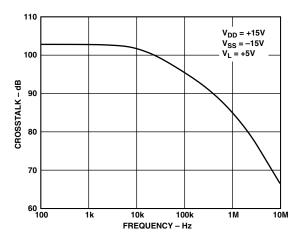


TPC 6. Leakage Currents as a Function of V_D (V_S)

REV. C _5_



TPC 7. Off Isolation vs. Frequency



TPC 8. Crosstalk vs. Frequency

TRENCH ISOLATION

In the ADG431A, ADG432A and ADG433A, an insulating oxide layer (trench) is placed between the NMOS and PMOS transistors of each CMOS switch. Parasitic junctions, which occur between the transistors in junction isolated switches, are eliminated, the result being a completely latch-up proof switch.

In junction isolation, the N and P wells of the PMOS and NMOS transistors from a diode that is reverse-biased under normal operation. However, during overvoltage conditions, this diode becomes forward biased. A silicon-controlled rectifier (SCR) type circuit is formed by the two transistors causing a significant amplification of the current which, in turn, leads to latch up. With trench isolation, this diode is removed, the result being a latch-up proof switch.

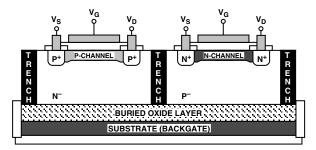


Figure 1. Trench Isolation

APPLICATION

Figure 2 illustrates a precise, fast sample-and-hold circuit. An AD845 is used as the input buffer while the output operational amplifier is an AD711. During the track mode, SW1 is closed and the output $V_{\rm OUT}$ follows the input signal $V_{\rm IN}$. In the hold mode, SW1 is opened and the signal is held by the hold capacitor $C_{\rm H}$.

Due to switch and capacitor leakage, the voltage on the hold capacitor will decrease with time. The ADG431/ADG432/ADG433 minimizes this droop due to its low leakage specifications. The droop rate is further minimized by the use of a polystyrene hold capacitor. The droop rate for the circuit shown is typically 30 μ V/ μ s.

A second switch SW2, which operates in parallel with SW1, is included in this circuit to reduce pedestal error. Since both switches will be at the same potential, they will have a differential effect on the op amp AD711 which will minimize charge injection effects. Pedestal error is also reduced by the compensation network $R_{\rm C}$ and $C_{\rm C}$. This compensation network also reduces the hold time glitch while optimizing the acquisition time. Using the illustrated op amps and component values, the pedestal error has a maximum value of 5 mV over the ± 10 V input range. Both the acquisition and settling times are 850 ns.

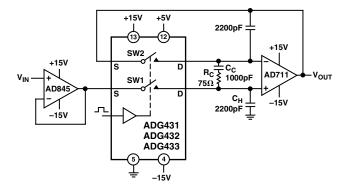
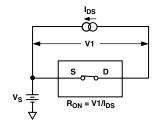


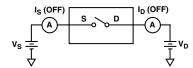
Figure 2. Fast, Accurate Sample-and-Hold

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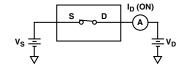
Test Circuits



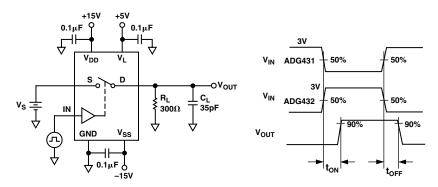
Test Circuit 1. On Resistance



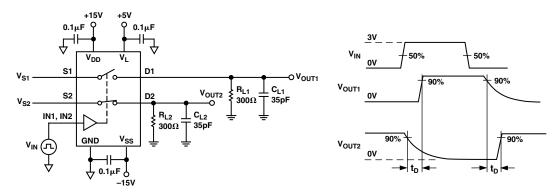
Test Circuit 2. Off Leakage



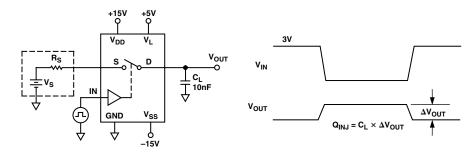
Test Circuit 3. On Leakage



Test Circuit 4. Switching Times

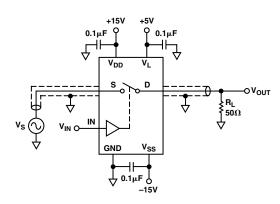


Test Circuit 5. Break-Before-Make Time Delay

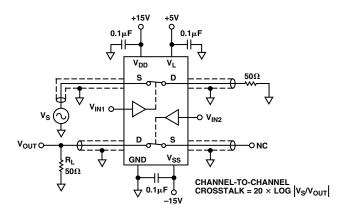


Test Circuit 6. Charge Injection

REV. C -7-



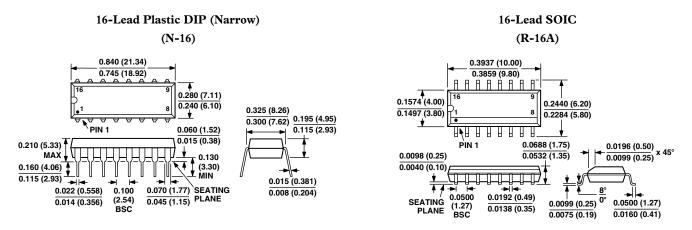
Test Circuit 7. Off Isolation



Test Circuit 8. Channel-to-Channel Crosstalk

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).



ADG431/ADG432/ADG433—Revision History

Location	Page
Data Sheet changed from REV. B to REV. C.	
Changes to Specifications Table (Dual Supply)	2
Changes to Specifications Table (Single Supply)	3
Changes to Absolute Maximum Ratings	4
Changes to Ordering Guide	4
16-Lead Cerdip deleted from Outline Dimensions	8

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